L Number	Hits	Search Text	DB	Time stamp
-	139321	a. = a,	USPAT;	2004/09/20 14:
			US-PGPUB; EPO; JPO; DERWENT; IBM TDB	
_	886566	gate	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/20 11:
-	103991	parasiti\$6	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/20 13:
-	476166	sti or isolating or isolation	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/20 11:
-	44573	field adj3 (oxide or insulat\$5)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/20 11:
_	369527	separat\$4 near4 (element or device or transistor)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/20 11:
-	836589	<pre>(sti or isolating or isolation) or (field adj3 (oxide or insulat\$5)) or (separat\$4 near4 (element or device or transistor))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/20 13:
-	451	<pre>(body near3 contact\$4) same gate same ((sti or isolating or isolation) or (field adj3 (oxide or insulat\$5)) or (separat\$4 near4 (element or device or transistor)))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/20 11:
-	193	((body near3 contact\$4) same gate same ((sti or isolating or isolation) or (field adj3 (oxide or insulat\$5)) or (separat\$4 near4 (element or device or transistor)))) and parasiti\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/20 13:
-	48279	(t or h) with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/20 13:
-	40618	soi or (si or silicon) adj2 insulat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/21 10:
-	836589	<pre>(sti or isolating or isolation) or (field adj3 (oxide or insulat\$5)) or (separat\$4 near4 (element or device or transistor))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/20 13:
-	103991	parasiti\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/20 14:
~	139321	body near3 contact\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/20 14:

	116		LIODAM -	2004/00/20 14.55
-	116	1 , , , , , , , , , , , , , , , , , , ,	USPAT;	2004/09/20 14:55
		silicon) adj2 insulat\$4) and ((sti or	US-PGPUB;	
		isolating or isolation) or (field adj3	EPO; JPO;	
		(oxide or insulat\$5)) or (separat\$4 near4	DERWENT;	
		(element or device or transistor))) and	IBM_TDB	
	l	parasiti\$6 and (body near3 contact\$4)		
-	62047	1	USPAT;	2004/09/20 14:56
		(tie or contact)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/00/00 14 57
_	3793	·	USPAT;	2004/09/20 14:57
		and (bodytie or body adj2 tie or substrate	US-PGPUB;	
		adj3 (tie or contact))	EPO; JPO;	
			DERWENT;	
		[IBM_TDB	/ /
-	2400		USPAT;	2004/09/20 14:57
		and (bodytie or body adj2 tie or substrate	US-PGPUB;	
		adj3 (tie or contact))) and ((sti or	EPO; JPO;	
		isolating or isolation) or (field adj3	DERWENT;	
		(oxide or insulat\$5)) or (separat\$4 near4	IBM_TDB	
		(element or device or transistor)))		
-	807	(((soi or (si or silicon) adj2 insulat\$4)	USPAT;	2004/09/20 14:58
		and (bodytie or body adj2 tie or substrate	US-PGPUB;	
		adj3 (tie or contact))) and ((sti or	EPO; JPO;	
		isolating or isolation) or (field adj3	DERWENT;	
		(oxide or insulat\$5)) or (separat\$4 near4	IBM_TDB	
		(element or device or transistor)))) and		
		parasiti\$6		
-	133	((((soi or (si or silicon) adj2 insulat\$4)	USPAT;	2004/09/20 14:59
		and (bodytie or body adj2 tie or substrate	US-PGPUB;	
		adj3 (tie or contact))) and ((sti or	EPO; JPO;	
		isolating or isolation) or (field adj3	DERWENT;	
ŀ		(oxide or insulat\$5)) or (separat\$4 near4	IBM_TDB	
		(element or device or transistor)))) and		
		parasiti\$6) and ((t or h) with gate)		
-	1782		USPAT;	2004/09/20 17:31
		438/296.ccls.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	521029	parasitic\$4 or kink or float\$4	USPAT;	2004/09/20 17:31
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	626	(438/151.ccls. or 438/221.ccls. or	USPAT;	2004/09/20 17:32
		438/296.ccls.) and (parasitic\$4 or kink or	US-PGPUB;	
		float\$4)	EPO; JPO;	1
			DERWENT;	
			IBM_TDB_	